

LM6161/LM6261/LM6361 High Speed Operational Amplifier

General Description

The LM6161 family of high-speed amplifiers exhibits an excellent speed-power product in delivering 300 V/ μ s and 50 MHz unity gain stability with only 5 mA of supply current. Further power savings and application convenience are possible by taking advantage of the wide dynamic range in operating supply voltage which extends all the way down to +5V

These amplifiers are built with National's VIP™ (Vertically Integrated PNP) process which provides fast PNP transistors that are true complements to the already fast NPN devices. This advanced junction-isolated process delivers high speed performance without the need for complex and expensive dielectric isolation.

Features

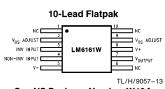
■ High slew rate	300 V/μs
■ High unity gain freq	50 MHz
■ Low supply current	5 mA
■ Fast settling	120 ns to 0.1%
■ Low differential gain	<0.1%
Low differential phase	0.1°
■ Wide supply range	4.75V to 32V

- Stable with unlimited capacitive load
- Well behaved; easy to apply

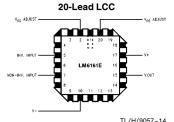
Applications

- Video amplifier
- High-frequency filter
- Wide-bandwidth signal conditioning
- Radar
- Sonar

Connection Diagrams



See NS Package Number W10A



See NS Package Number E20A

Vos Adjust 8 	∨+ 7 	^V оит 6 	N/C 5	
]	
	<u> </u>			
1 V _{OS} Adjust	2 INV input	3 NI input	4 V-	-
			TL/H/	9057-5

See NS Package Number J08A, N08E or M08A

		NSC			
$\begin{tabular}{ll} Military \\ -55^{\circ}C \le T_{\mbox{\scriptsize A}} \le +125^{\circ}C \end{tabular}$	Industrial -25°C ≤ T _A ≤ +85°C	$\begin{array}{c} \text{Commercial} \\ 0^{\circ}\text{C} \leq \text{T}_{\text{A}} \leq +70^{\circ}\text{C} \end{array}$	Package	Drawing	
	LM6261N	LM6361N	8-Pin Molded DIP	N08E	
LM6161J/883 5962-8962101PA		LM6361J	8-Pin Ceramic DIP	J08A	
	LM6261M	LM6361M	8-Pin Molded Surface Mt.	M08A	
LM6161E/883 5962-89621012A			20-Lead LCC	E20A	
LM6161W/883 5962-8962101HA			10-Pin Ceramic Flatpak	W10A	

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Absolute Maximum Ratings (Note 12)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage ($V^+ - V^-$) Differential Input Voltage (Note 8) $\pm 8V$ Common-Mode Voltage Range (Note 10) $(V^+ - 0.7V)$ to $(V^- + 0.7V)$ Continuous Output Short Circuit to GND (Note 1) Soldering Information Dual-In-Line Package (N, J) Soldering (10 sec.) 260°C

Small Outline Package (M) Vapor Phase (60 sec.) 215°C

Infrared (15 sec.) 220°C See AN-450 "Surface Mounting Methods and Their Effect on Product Reliability" for other methods of soldering surface mount devices.

Storage Temp Range -65°C to +150°C Max Junction Temperature 150°C ESD Tolerance (Notes 6 and 7) $\pm\,700V$

Operating Ratings (Note 12)

Temperature Range (Note 2)

 $\begin{array}{l} -55^{\circ}C \leq T_{J} \leq +125^{\circ}C \\ -25^{\circ}C \leq T_{J} \leq +85^{\circ}C \\ 0^{\circ}C \leq T_{J} \leq +70^{\circ}C \end{array}$ LM6161 LM6261 LM6361 4.75V to 32V Supply Voltage Range

DC Electrical Characteristics

The following specifications apply for Supply Voltage $=\pm15$ V, $V_{CM}=0$, $R_L\geq100$ k Ω and $R_S=50\Omega$ unless otherwise noted. **Boldface** limits apply for $T_J = T_{MIN}$ to T_{MAX} ; all other limits $T_J = 25$ °C.

Symbol	Parameter	Conditions	Тур	LM6161	LM6261	LM6361	Units
				Limit (Notes 3, 11)	Limit (Note 3)	Limit (Note 3)	
V _{OS}	Input Offset Voltage		5	7 10	7 9	20 22	mV Max
V _{OS} Drift	Input Offset Voltage Average Drift		10				μV/°C
I _b	Input Bias Current		2	3 6	3 5	5 6	μA Max
I _{OS}	Input Offset Current		150	350 800	350 600	1500 1900	nA Max
I _{OS} Drift	Input Offset Current Average Drift		0.4				nA/°C
R _{IN}	Input Resistance	Differential	325				kΩ
C _{IN}	Input Capacitance	A _V = +1 @ 10 MHz	1.5				pF
,,,	Large Signal Voltage Gain	$V_{OUT} = \pm 10V,$ $R_L = 2 \text{ k}\Omega \text{ (Note 9)}$	750	550 300	550 400	400 350	V/V Min
		$R_L = 10 \text{ k}\Omega \text{ (Note 9)}$	2900				V/V
OIVI I	M Input Common-Mode Supply Voltage Range	1,	+14.0	+13.9 + 13.8	+ 13.9 + 13.8	+ 13.8 + 13.7	Volts Min
			-13.2	−12.9 − 12.7	-12.9 - 12.7	-12.8 - 12.7	Volts Min
		Supply = +5V (Note 4)	4.0	3.9 3.8	3.9 3.8	3.8 3.7	Volts Min
			1.8	2.0 2.2	2.0 2.2	2.1 2.2	Volts Max
CMRR	Common-Mode Rejection Ratio	$-10V \le V_{CM} \le +10V$	94	80 74	80 76	72 70	dB Min
PSRR	Power Supply Rejection Ratio	$\pm 10 \text{V} \le \text{V}^{\pm} \le \pm 16 \text{V}$	90	80 74	80 76	72 70	dB Min
Vo	Output Voltage Swing	Supply = $\pm 15V$ and R _L = $2 k\Omega$	+14.2	+ 13.5 + 13.3	+ 13.5 + 13.3	+ 13.4 + 13.3	Volts Min
			-13.4	-13.0 - 12.7	-13.0 - 12.8	-12.9 - 12.8	Volts Min

DC Electrical Characteristics (Continued)

The following specifications apply for Supply Voltage $=\pm15$ V, $V_{CM}=0$, $R_L\geq 100$ k Ω and $R_S=50\Omega$ unless otherwise noted. **Boldface** limits apply for $T_J=T_{MIN}$ to T_{MAX} ; all other limits $T_J=25^\circ C$.

Symbol	Parameter	Conditions	Тур	LM6161	LM6261	LM6361	Units
				Limit (Notes 3, 11)	Limit (Note 3)	Limit (Note 3)	
V _O (Continued)	Output Voltage Swing (Continued)	Supply = $+5V$ and R _L = $2 k\Omega$	4.2	3.5 3.3	3.5 3.3	3.4 3.3	Volts Min
	(Note 4)	1.3	1.7 2.0	1.7 1.9	1.8 1.9	Volts Max	
	Output Short Circuit Current	Source	65	30 20	30 25	30 25	mA Min
	Sink	Sink	65	30 20	30 25	30 25	mA Min
IS	Supply Current		5.0	6.5 6.8	6.5 6.7	6.8 6.9	mA Max

AC Electrical Characteristics

The following specifications apply for Supply Voltage $=\pm$ 15V, $V_{CM}=0$, $R_L\geq 100$ k Ω and $R_S=50\Omega$ unless otherwise noted. **Boldface** limits apply for $T_J=T_{MIN}$ to T_{MAX} ; all other limits $T_J=25^{\circ}C$.

				LM6161	LM6261	LM6361	
Symbol	Parameter	Conditions	Тур	Limit (Notes 3, 11)	Limit (Note 3)	Limit (Note 3)	Units
GBW	Gain-Bandwidth Product	@ f = 20 MHz	50	40 30	40 35	35 32	MHz Min
		Supply = $\pm 5V$	35				MHz
SR	Slew Rate	A _V = +1 (Note 8)	300	200 180	200 180	200 180	V/μs Min
		Supply = $\pm 5V$ (Note 8)	200				V/μs
PBW	Power Bandwidth	$V_{OUT} = 20 V_{PP}$	4.5				MHz
t _S	Settling Time	10V Step to 0.1% $A_V = -1$, $R_L = 2 k\Omega$	120				ns
φm	Phase Margin		45				Deg
A _D	Differential Gain	NTSC, $A_V = +4$	< 0.1				%
φD	Differential Phase	NTSC, $A_V = +4$	0.1				Deg
e _{np-p}	Input Noise Voltage	f = 10 kHz	15				nV/√ Hz
i _{np-p}	Input Noise Current	f = 10 kHz	1.5				pA/√Hz

Note 1: Continuous short-circuit operation at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C.

Note 2: The typical junction-to-ambient thermal resistance of the molded plastic DIP (N) is 105°C/W, the molded plastic SO (M) package is 155°C/W, and the cerdip (J) package is 125°C/W. All numbers apply for packages soldered directly into a printed circuit board.

Note 3: Limits are guaranteed by testing or correlation.

Note 4: For single supply operation, the following conditions apply: V⁺ = 5V, V⁻ = 0V, V_{CM} = 2.5V, V_{OUT} = 2.5V. Pin 1 & Pin 8 (Vos Adjust) are each connected to Pin 4 (V⁻) to realize maximum output swing. This connection will degrade V_{OS}, V_{OS} Drift, and Input Voltage Noise.

Note 5: $C_L \le 5 \text{ pF}.$

Note 6: In order to achieve optimum AC performance, the input stage was designed without protective clamps. Exceeding the maximum differential input voltage results in reverse breakdown of the base-emitter junction of one of the input transistors and probable degradation of the input parameters (especially Vos, los, and Noise)

Note 7: The average voltage that the weakest pin combinations (those involving Pin 2 or Pin 3) can withstand and still conform to the datasheet limits. The test circuit used consists of the human body model of 100 pF in series with 1500 Ω .

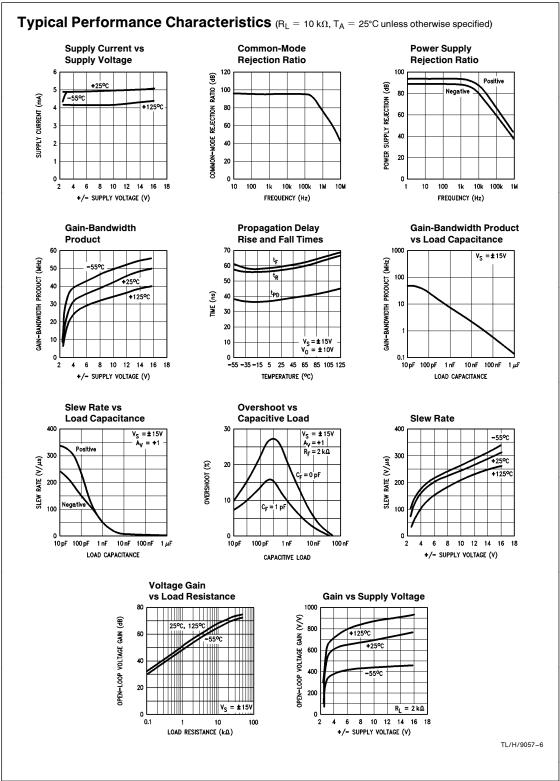
Note 8: $V_{IN} = 8V$ step. For supply $= \pm 5V$, $V_{IN} = 5V$ step.

Note 9: Voltage Gain is the total output swing (20V) divided by the input signal required to produce that swing.

Note 10: The voltage between V⁺ and either input pin must not exceed 36V.

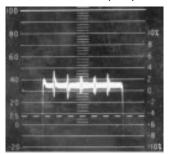
Note 11: A military RETS electrical test specification is available on request. At the time of printing, the RETS6161X specs complied with all **Boldface** limits in this column.

Note 12: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed.

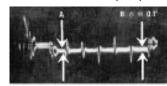


Typical Performance Characteristics (R_L = 10 k Ω , T_A = 25°C unless otherwise specified) (Continued)

Differential Gain (Note)



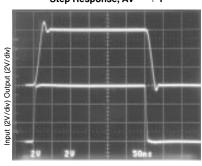
Differential Phase (Note)



Note: Differential gain and differential phase measured for four series LM6361 op amps configured as unity-gain followers, in series with an LM6321 buffer. Error added by LM6321 is negligible. Test performed using Tektronix Type 520 NTSC test system.

TL/H/9057-7

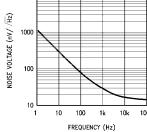
Step Response; Av = +1



(50 ns/div)

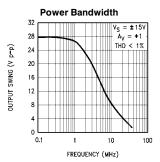
TL/H/9057-1

Input Noise Voltage 10,000



Input Noise Current 1000 NOISE CURRENT (pA//Hz) 10 100

FREQUENCY (Hz)



TL/H/9057-9

Typical Performance Characteristics (R_L = 10 k Ω , T_A = 25°C unless otherwise specified) (Continued) Open-Loop Frequency Response **Output Impedence** Open-Loop Frequency Response (Open-Loop) 100 OPEN-LOOP VOLTAGE GAIN (dB) 50 OPEN-LOOP VOLTAGE GAIN (dB) OUTPUT IMPEDANCE (OHMS) PHASE SHIFT (degrees) 40 10k 30 PHASE SHIFT (degrees) 10 PHASE 0 100 -10 -20 450 -20 450 10k 100k 1 M 10M 100M 1G 10M 10k 100k 1k 1M 10M 100M 1G 1k FREQUENCY (Hz) FREQUENCY (Hz) FREQUENCY (Hz) **Common-Mode Input Bias Current vs** Saturation Voltage **Output Saturation Voltage** Common-Mode Voltage DUTPUT SATURATION VOLTAGE (V) INPUT SATURATION VOLTAGE (V) INPUT BIAS CURRENT (µA) -55°C +125°C 8 10 12 14 16 18 6 8 10 12 14 16 18 **-**5 0 +/- SUPPLY VOLTAGE (V) +/- SUPPLY VOLTAGE (V) COMMON-MODE VOLTAGE (V) TL/H/9057-12 **Simplified Schematic 7** ∨ + 6 V_{OUT} INV input 3 NI input **(** 600Ω 600Ω 4 ∨-⇧ V_{OS} Adjust 8 TL/H/9057-3

Applications Tips

The LM6361 has been compensated for unity-gain operation. Since this compensation involved adding emitter-degeneration resistors to the op amp's input stage, the openloop gain was reduced as the stability increased. Gain error due to reduced A_{VOL} is most apparent at high gains; thus, for gains between 5 and 25, the less-compensated LM6364 should be used, and the uncompensated LM6365 is appropriate for gains of 25 or more. The LM6361, LM6364, and LM6365 have the same high slew rate, regardless of their compensation.

The LM6361 is unusually tolerant of capacitive loads. Most op amps tend to oscillate when their load capacitance is greater than about 200 pF (especially in low-gain circuits). The LM6361's compensation is effectively increased with load capacitance, reducing its bandwidth and increasing its stability

Power supply bypassing is not as critical for the LM6361 as it is for other op amps in its speed class. Bypassing will,

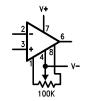
however, improve the stability and transient response and is recommended for every design. 0.01 μF to 0.1 μF ceramic capacitors should be used (from each supply "rail" to ground); if the device is far away from its power supply source, an additional 2.2 μF to 10 μF of tantalum may provide extra noise reduction.

Keep all leads short to reduce stray capacitance and lead inductance, and make sure ground paths are low-impedance, especially where heavier currents will be flowing. Stray capacitance in the circuit layout can cause signal coupling across adjacent nodes and can cause gain to unintentionally vary with frequency.

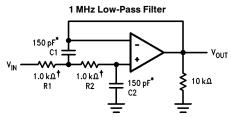
Breadboarded circuits will work best if they are built using generic PC boards with a good ground plane. If the op amps are used with sockets, as opposed to being soldered into the circuit, the additional input capacitance may degrade circuit performance.

Typical Applications

Offset Voltage Adjustment



TL/H/9057-4



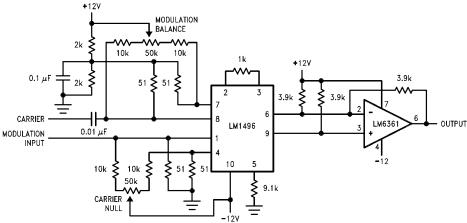
TL/H/9057-10

†1% tolerance

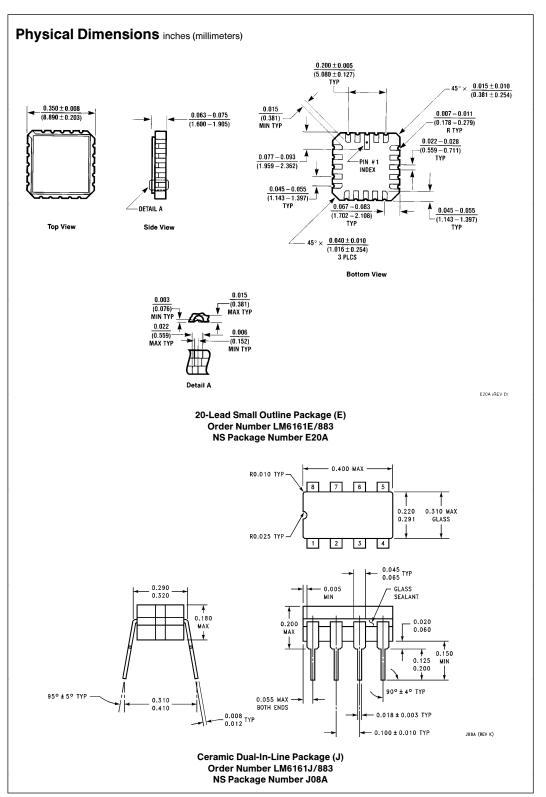
*Matching determines filter precision

 $f_{\rm C} = (2\pi \sqrt{({\rm R1~R2~C1~C2})})^{-1}$

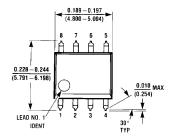
Modulator with Differential-to-Single-Ended Converter

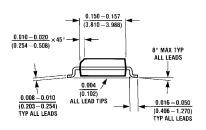


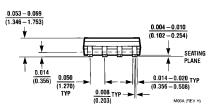
TL/H/9057-11



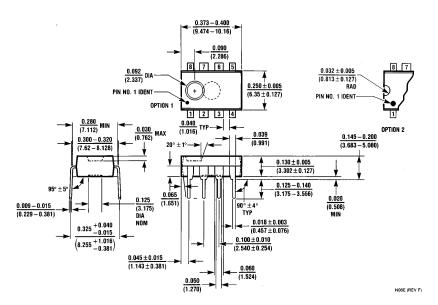
Physical Dimensions inches (millimeters) (Continued)





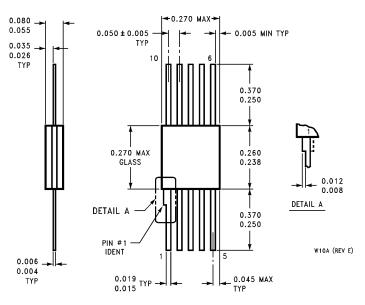


Molded Package SO (M) Order Number LM6261M or LM6361M NS Package Number M08A



Molded Dual-In-Line Package (N)
Order Number LM6261N or LM6361N
NS Package Number N08E

Physical Dimensions inches (millimeters) (Continued)



10-Pin Ceramic Flatpak Order Number LM6161W/883 NS Package Number W10A

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